

Woo Kyun Kim

List of Publications by Year in descending order

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Version: 2024-02-01

12
papers

204
citations

1478505

6
h-index

1588992

8
g-index

12
all docs

12
docs citations

12
times ranked

236
citing authors

#	ARTICLE	IF	CITATIONS
1	Roadmap on multiscale materials modeling. Modelling and Simulation in Materials Science and Engineering, 2020, 28, 043001.	2.0	100
2	A molecular dynamics study on atomistic mechanisms of nano-scale cutting process of sapphire. Journal of Mechanical Science and Technology, 2017, 31, 4353-4362.	1.5	28
3	Molecular dynamics simulation of the uniaxial tensile test of silicon nanowires using the MEAM potential. Mechanics of Materials, 2019, 137, 103140.	3.2	27
4	Nanoscale indentation and scratching tests of single crystal sapphire using molecular dynamics simulation. Computational Materials Science, 2019, 170, 109195.	3.0	21
5	Molecular dynamics study on friction of polycrystalline graphene. Computational Materials Science, 2017, 137, 346-361.	3.0	13
6	Role of multigrain structure on friction of graphene layers. Computational Materials Science, 2019, 165, 23-33.	3.0	6
7	Effects of Langevin friction and time steps in the molecular dynamics simulation of nanoindentation. Molecular Simulation, 2020, 46, 911-922.	2.0	3
8	A comparison study between the Lennard-Jones and DRIP potentials for friction of graphene layers. Computational Materials Science, 2020, 180, 109723.	3.0	3
9	Argon cluster sputter yield: Molecular dynamics simulations on silicon and equation for estimating total sputter yield. Surface and Interface Analysis, 0, , .	1.8	2
10	A hybrid quasicontinuum method. International Journal for Numerical Methods in Engineering, 2019, 117, 1059-1078.	2.8	1
11	Role of boundary conditions and thermostats in the uniaxial tensile loading of silicon nanowires. Computational Materials Science, 2020, 178, 109636.	3.0	0
12	Free energy calculation and ghost force correction for QC. International Journal for Numerical Methods in Engineering, 0, , .	2.8	0